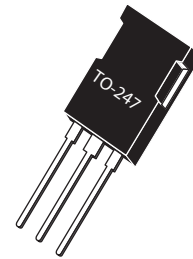



Ultra Fast NPT - IGBT®

The Ultra Fast NPT - IGBT® is a new generation of high voltage power IGBTs. Using Non-Punch-Through Technology, the Ultra Fast NPT-IGBT® offers superior ruggedness and ultrafast switching speed.



Features

- Low Saturation Voltage
- Low Tail Current
- RoHS Compliant 
- Short Circuit Withstand Rated
- High Frequency Switching to 50KHz
- Ultra Low Leakage Current

Combi (IGBT and Diode)



Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is recommended for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

MAXIMUM RATINGS

 All Ratings: $T_C = 25^\circ C$ unless otherwise specified.

Symbol	Parameter	Ratings	Unit
V_{CES}	Collector Emitter Voltage	1200	V
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ C$	88	A
I_{C2}	Continuous Collector Current @ $T_C = 100^\circ C$	40	
I_{CM}	Pulsed Collector Current ^①	160	
SCWT	Short Circuit Withstand Time: $V_{CE} = 600V, V_{GE} = 15V, T_C = 125^\circ C$	10	μs
P_D	Total Power Dissipation @ $T_C = 25^\circ C$	500	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ C$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 1.0mA$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 2.0mA, T_J = 25^\circ C$)	3	4.5	6.0	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 40A, T_J = 25^\circ C$)		2.5	3.2	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 40A, T_J = 125^\circ C$)		3.5		
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 88A, T_J = 25^\circ C$)		3.2		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 25^\circ C$) ^②		20	1100	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_J = 125^\circ C$) ^②		200		
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 250	nA


CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT40GR120B2D30

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1MHz$		3980		pF
C_{oes}	Output Capacitance			320		
C_{res}	Reverse Transfer Capacitance			80		
V_{GEP}	Gate to Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 40A$		7		V
$Q_g^{(3)}$	Total Gate Charge			210		nC
Q_{ge}	Gate-Emitter Charge			25		
Q_{gc}	Gate- Collector Charge			90		
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 40A$		22		ns
t_r	Current Rise Time			25		
$t_{d(off)}$	Turn-Off Delay Time			163		
t_f	Current Fall Time			40		
$E_{on2}^{(5)}$	Turn-On Switching Energy	$R_G = 4.3 \Omega^{(4)}$ $T_J = +25^\circ C$		1375	3000	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			906	1650	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 40A$		22		ns
t_r	Current Rise Time			25		
$t_{d(off)}$	Turn-Off Delay Time			185		
t_f	Current Fall Time			47		
$E_{on2}^{(5)}$	Turn-On Switching Energy	$R_G = 4.3 \Omega^{(4)}$ $T_J = +125^\circ C$		1916	3500	μJ
$E_{off}^{(6)}$	Turn-Off Switching Energy			1186	2500	

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)			.25	$^\circ C/W$
	Junction to Case Thermal Resistance (Diode)			.80	
$R_{\theta JA}$	Junction to Ambient Thermal Resistance			40	
W_T	Package Weight		.22		oz
			6.2		g

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width < 380 μs , duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT40GR120B2D30

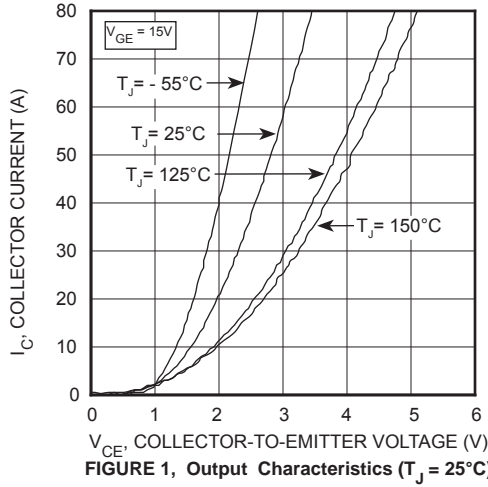


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

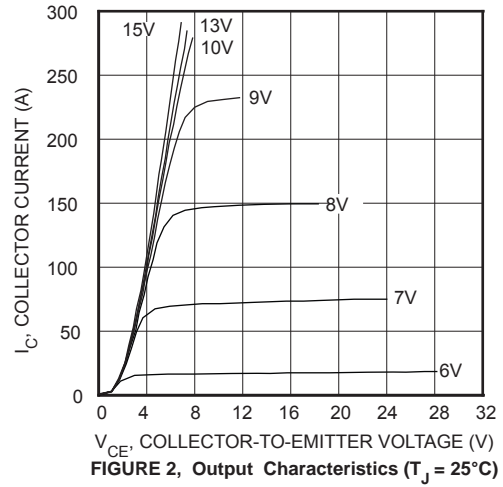


FIGURE 2, Output Characteristics ($T_J = 25^\circ\text{C}$)

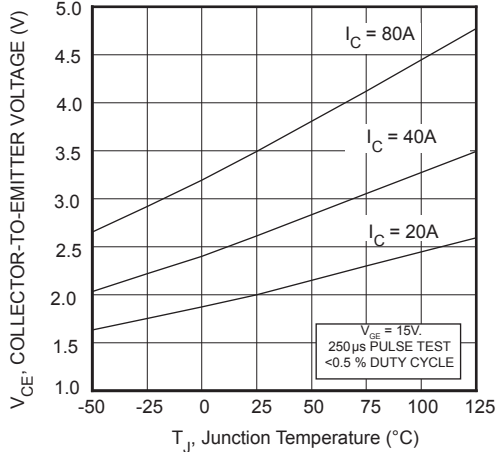


FIGURE 3, On State Voltage vs Junction Temperature

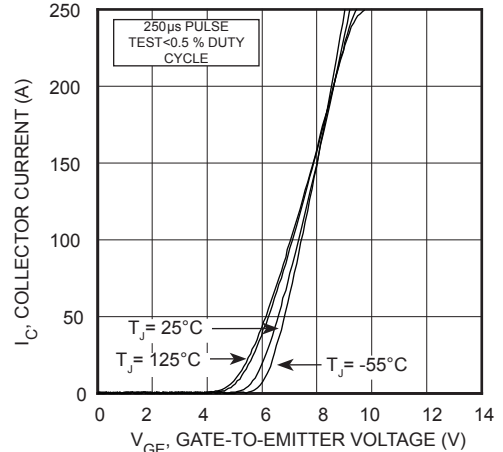


FIGURE 4, Transfer Characteristics

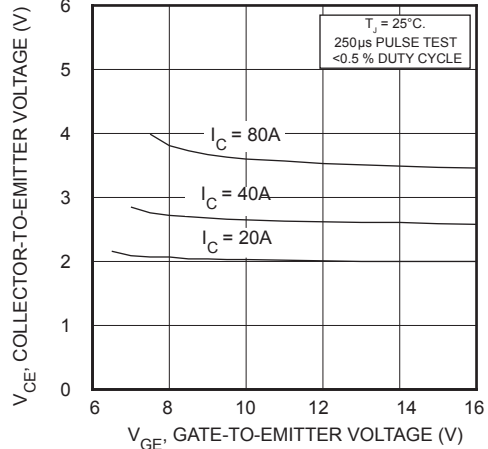


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

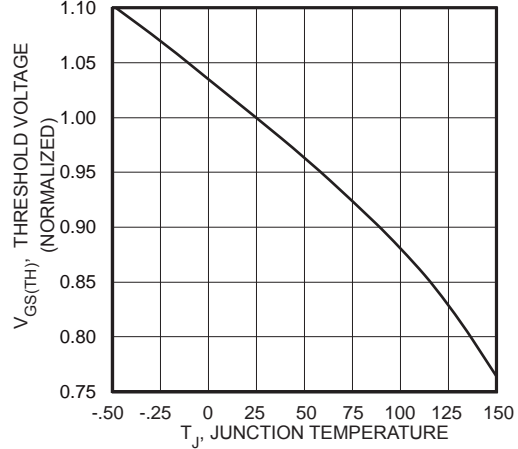


FIGURE 6, Threshold Voltage vs Junction Temperature

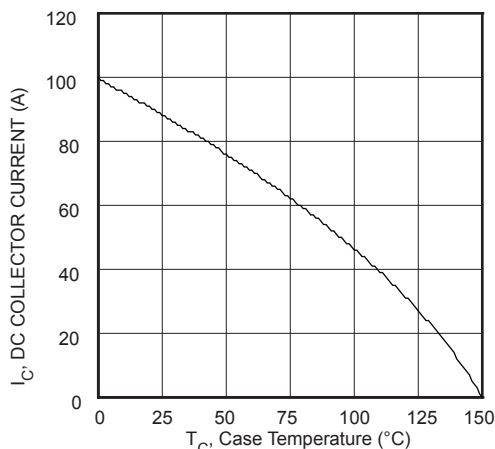


FIGURE 7, DC Collector Current vs Case Temperature

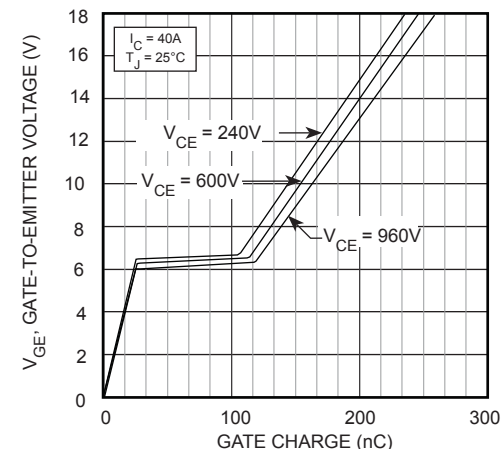


FIGURE 8, Gate charge

TYPICAL PERFORMANCE CURVES

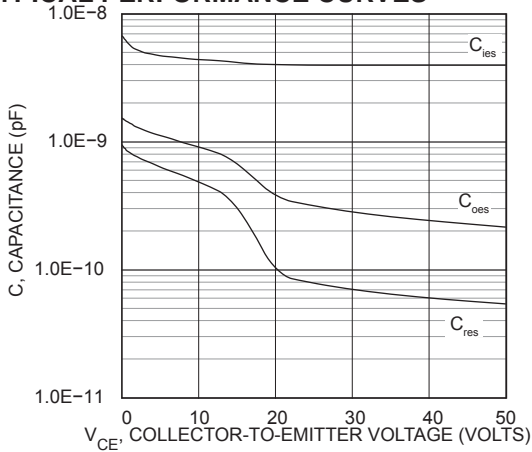


FIGURE 9, Capacitance vs Collector-To-Emitter Voltage

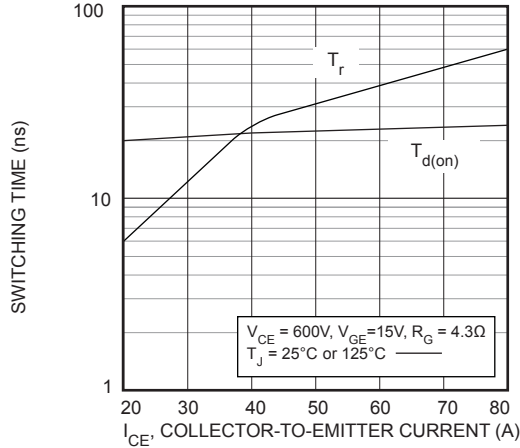


FIGURE 11, Turn-On Time vs Collector Current

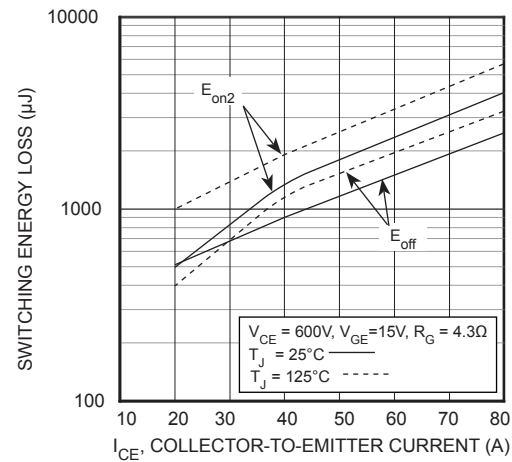


FIGURE 13, Energy Loss vs Collector Current

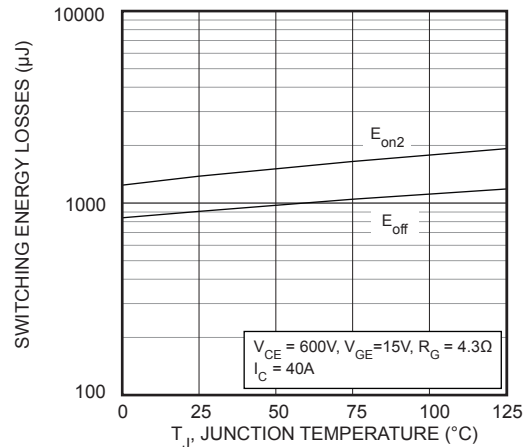


FIGURE 15, Energy Losses vs Junction Temperature

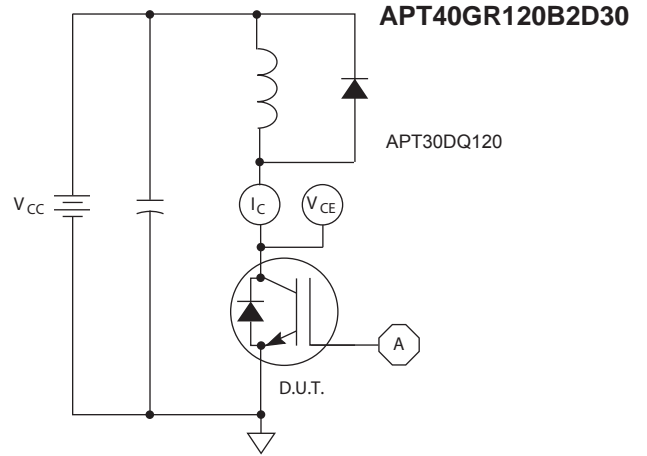


FIGURE 10, Inductive Switching Test Circuit

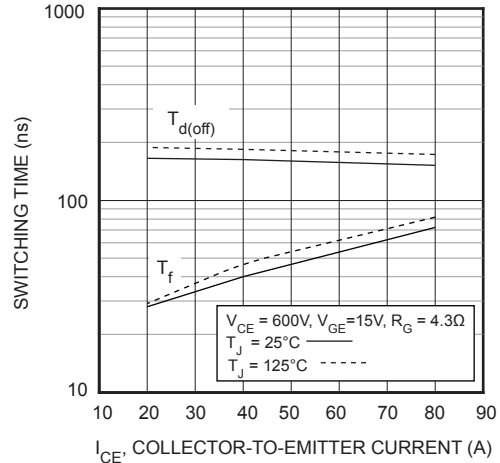


FIGURE 12, Turn-Off Time vs Collector Current

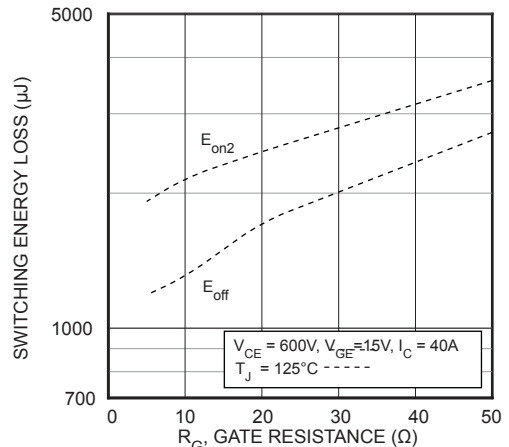


FIGURE 14, Energy Loss vs Gate Resistance

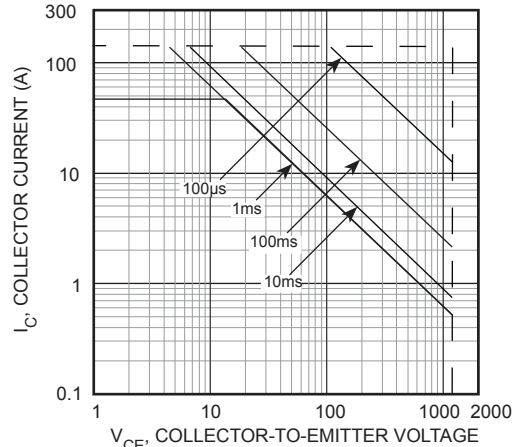


FIGURE 16, Minimum Switching Safe Operating Area

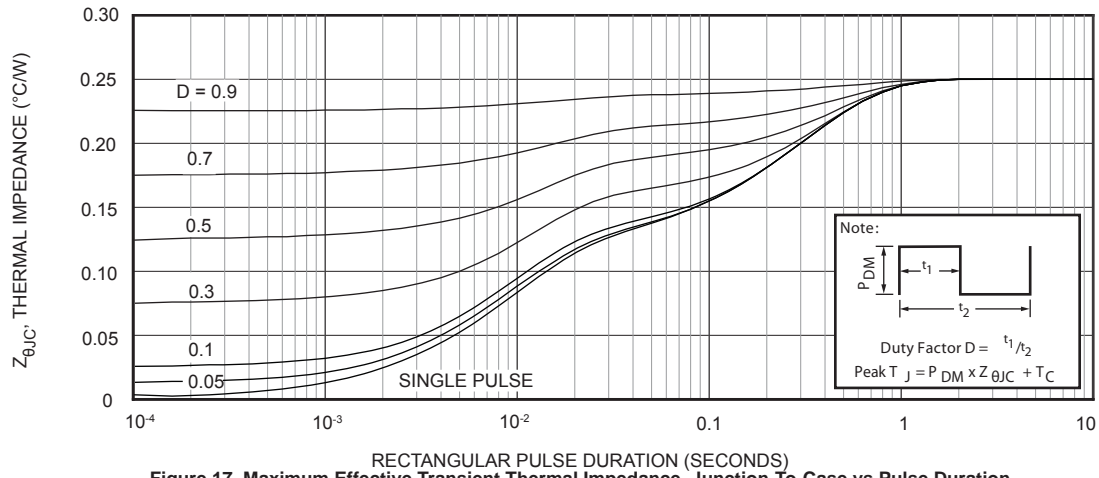


Figure 17, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT40GR120B2D30		UNIT
$I_{F(AV)}$	Maximum Average Forward Current ($T_C = 110^\circ\text{C}$, Duty Cycle = 0.5)	30		Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	43		
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	210		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage		$I_F = 30\text{A}$	2.8	Volts
			$I_F = 60\text{A}$	3.4	
			$I_F = 30\text{A}, T_J = 125^\circ\text{C}$	2.1	

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	26		ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 25^\circ\text{C}$	-	320		
Q_{rr}	Reverse Recovery Charge		-	545		nC
I_{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	435		ns
Q_{rr}	Reverse Recovery Charge		-	2100		nC
I_{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	180		ns
Q_{rr}	Reverse Recovery Charge		-	2975		nC
I_{RRM}	Maximum Reverse Recovery Current		-	28		Amps

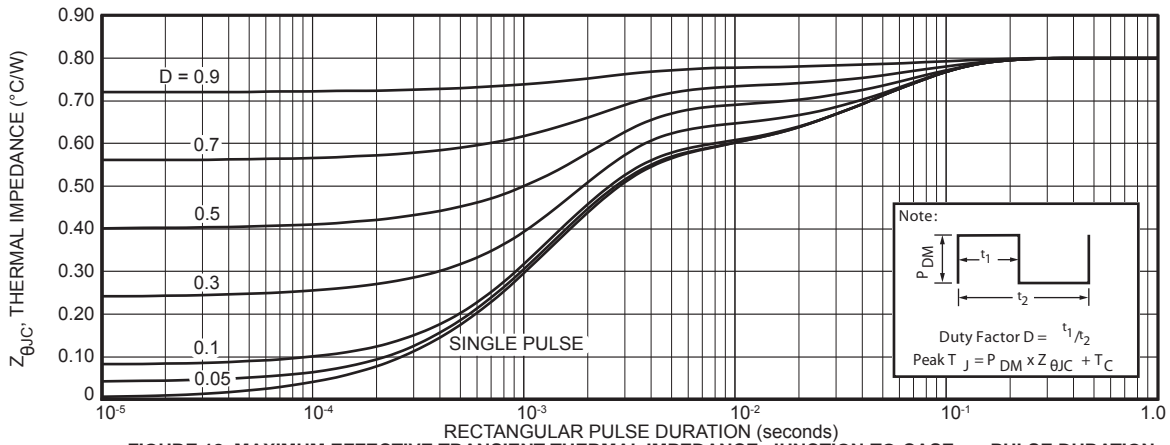


FIGURE 18. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

TYPICAL PERFORMANCE CURVES

APT40GR120B2D30

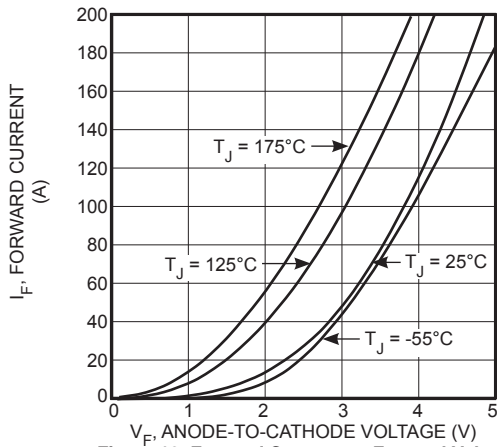


Figure 19. Forward Current vs. Forward Voltage

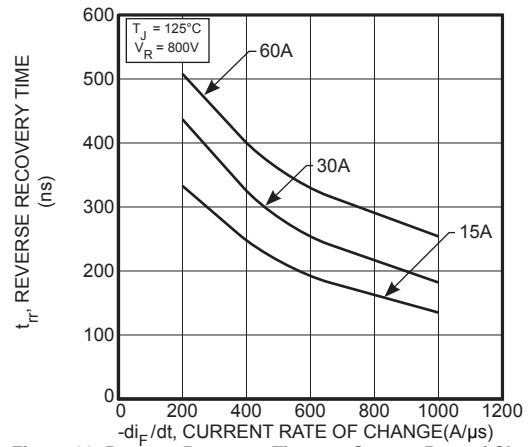


Figure 20. Reverse Recovery Time vs. Current Rate of Change

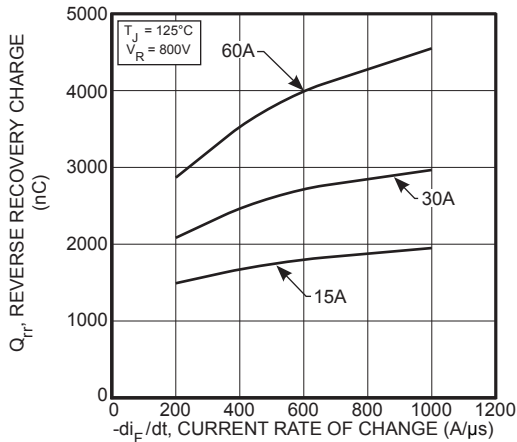


Figure 21. Reverse Recovery Charge vs. Current Rate of Change

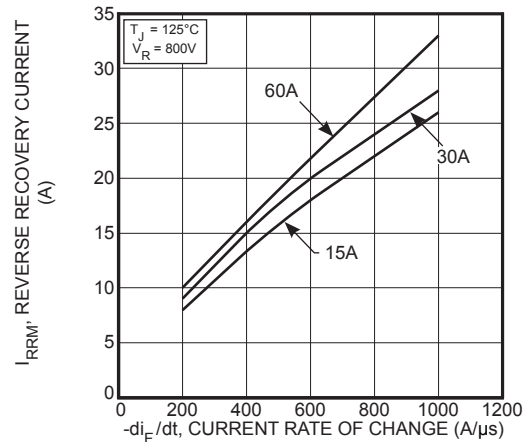


Figure 22. Reverse Recovery Current vs. Current Rate of Change

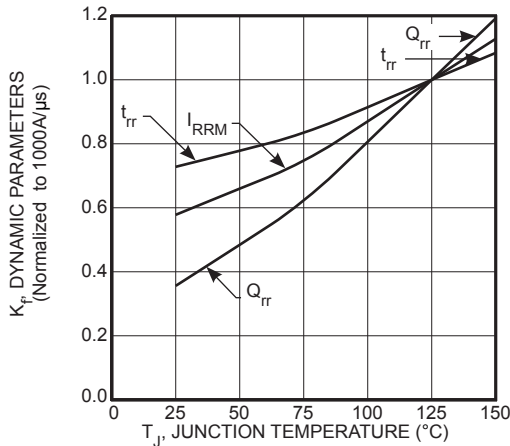


Figure 23. Dynamic Parameters vs. Junction Temperature

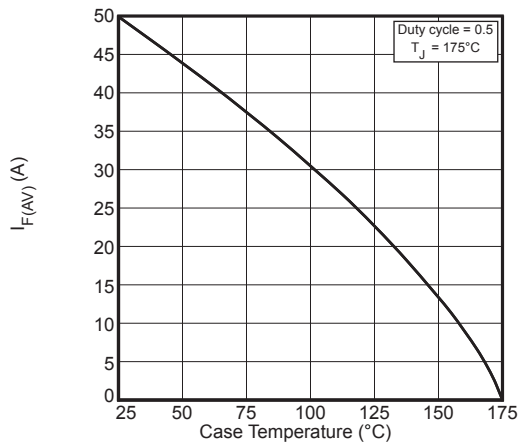


Figure 24. Maximum Average Forward Current vs. Case Temperature

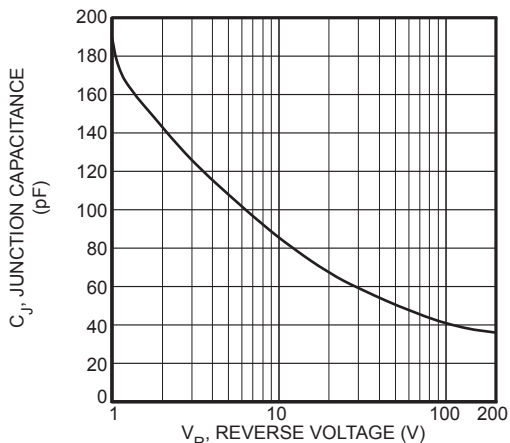


Figure 25. Junction Capacitance vs. Reverse Voltage

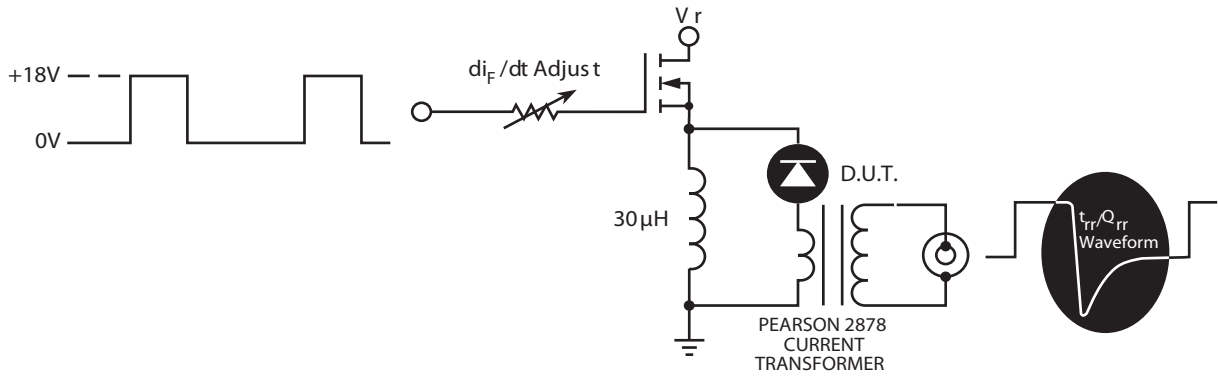


Figure 26. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current
- 4 t_{rr} - Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25 I_{RRM} passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

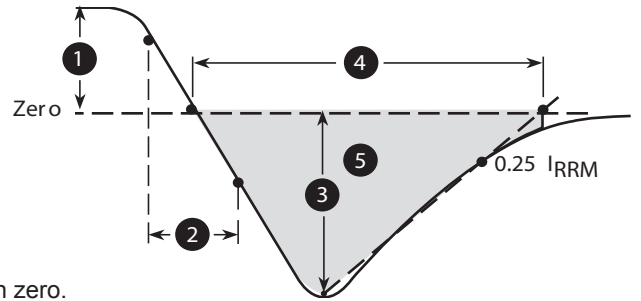
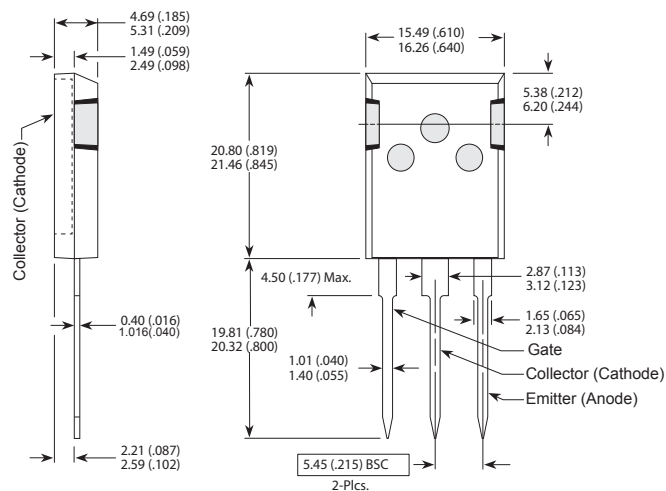


Figure 27. Diode Reverse Recovery Waveform Definition

T-MAX[®] (B2) Package Outline

e3 100% Sn Plated



These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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